



# TECHNICAL SPECIFICATION

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**Nanomanufacturing – Key control characteristics –  
Part 8-4: Metal-oxide interfacial devices – Activation energy of electronic trap  
states: Low-frequency-noise spectroscopy**

INTERNATIONAL  
ELECTROTECHNICAL  
COMMISSION

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## INTERNATIONAL ELECTROTECHNICAL COMMISSION

**NANOMANUFACTURING –  
KEY CONTROL CHARACTERISTICS –**

**Part 8-4: Metal-oxide interfacial devices – Activation energy of electronic trap states: Low-frequency-noise spectroscopy**

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IEC TS 62607-8-4 has been prepared by IEC technical committee 113: Nanotechnology for electrotechnical products and systems. It is a Technical Specification.

The text of this Technical Specification is based on the following documents:

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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this Technical Specification is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at [www.iec.ch/members\\_experts/refdocs](http://www.iec.ch/members_experts/refdocs). The main document types developed by IEC are described in greater detail at [www.iec.ch/publications](http://www.iec.ch/publications).

A list of all parts in the IEC 62607 series, published under the general title *Nanomanufacturing – Key control characteristics*, can be found on the IEC website.

Future subparts of IEC 62607-8 will carry the new general title *Metal-oxide interfacial devices* as cited above. Titles of existing subparts in this series will be updated at the time of the next edition.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under [webstore.iec.ch](http://webstore.iec.ch) in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn, or
- revised.

## INTRODUCTION

Nano-enabled metal-oxide interfaces, such as an oxide nanolayer sandwiched by metal electrodes, are the essential components of IoT and AI devices for computing. Nano-enabled functions derived from the nanoscale metal-oxide interface and the oxide nanolayer appear, such as a significant change in electrical resistance. Analogue resistance change is the typical characteristic which possesses the large potential for non-von Neumann information processing. More concretely, the metal-oxide interfacial device is an indispensable element in the product-sum circuit that records the learning process as the analogue resistance change. It is known that the analogue resistance change occurs electronically in oxide interfacial layers regardless of the filamentary conductance. Since the electrical resistance is affected by electrons scattering in a material, it is extremely important to standardize the technique for evaluating electron traps in that material. Low-frequency-noise spectroscopy (LFNS) measurement is the powerful and unique tool to evaluate the activation energy of the electron trap states, which is one of the most essential electronic properties – especially in devices with the nano-scaled conductive path.

This document specifies a measurement protocol to evaluate the electronic trap states by LFNS in nano-enabled metal-oxide interfacial devices.

## NANOMANUFACTURING – KEY CONTROL CHARACTERISTICS –

### Part 8-4: Metal-oxide interfacial devices – Activation energy of electronic trap states: Low-frequency-noise spectroscopy

#### 1 Scope

This part of IEC 62607 specifies a measurement protocol to determine the key control characteristic

- activation energy of electronic trap states

for metal-oxide interfacial devices by

- low-frequency-noise spectroscopy

The noise spectra peak temperatures are obtained within a designated temperature range. Activation energies are then calculated based on the frequency dependence of the peak temperatures to analyse the energy levels associated with the electronic trap states. The activation energy is determined by the temperature dependence of the capture time at electron traps under the assumption that it is described by an Arrhenius function.

- In metal-oxide interfacial devices, electrical conductance is observed through an oxide nanolayer sandwiched between metal electrodes.
- The size of the conductive path in metal-oxide interfacial devices is dependent on the current value and is usually nanoscale in diameter, taking the form of a filamentary wire. This evaluation method is useful for analysing the electronic trap states in nanowires and other miniaturized devices that have nanolayers.

#### 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

ISO/TS 80004-1, *Nanotechnologies – Vocabulary – Part 1: Core terms*